

TLVx369 具有零交叉失真的成本优化型 800nA、1.8V、轨到轨 I/O 运算放大器

1 特性

- 成本优化型精密放大器，具有毫微功耗：800nA/通道（典型值）
- 低偏移电压：400 μ V（典型值）
- 轨到轨输入和输出
- 零交叉失真
- 低偏移漂移：0.5 μ V/°C（典型值）
- 增益带宽积：850MHz
- 电源电压：1.8V 至 5.5V
- 微型封装：SC70-5、VSSOP-8

2 应用

- 血糖仪
- 测试设备
- 低功耗传感器信号调节
- 便携式设备

3 说明

TLV369 系列单通道和双通道运算放大器是成本优化型 1.8V 毫微功耗放大器的典型代表。

该系列放大器由 1.8V 至 5.5V 的单电源供电运行，并且配有零交叉失真电路，可在整个共模输入范围内保持较高线性度且无交叉失真，从而实现真正的轨到轨输入。该系列还兼容符合行业标准的 3.0V、3.3V 和 5.0V 标称电压。

TLV369（单通道版本）采用 5 引脚 SC70 封装。

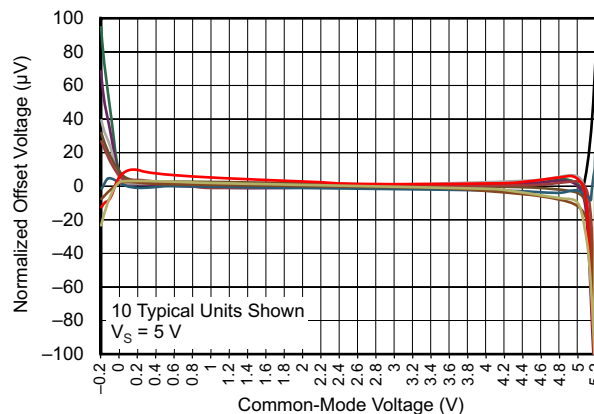
TLV2369（双通道版本）采用 8 引脚超薄小外形尺寸（VSSOP）和小外形尺寸集成电路（SOIC）封装。

器件信息⁽¹⁾

器件型号	封装	封装尺寸（标称值）
TLV369	SC70 (5)	2.00mm × 1.25mm
TLV2369	超薄小外形尺寸封装 (VSSOP) (8)	3.00mm × 3.00mm
	SOIC (8)	4.90mm × 3.91mm

(1) 要了解所有可用封装，请见数据表末尾的可订购产品附录。

TLV369 系列消除了整个电源电压范围内的交叉失真



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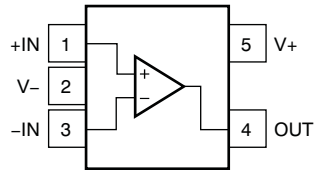
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4 修订历史记录

日期	修订版本	注释
2016 年 5 月	*	首次发布。

5 Pin Configuration and Functions

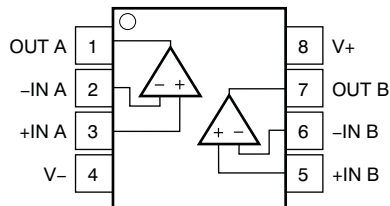
**TLV369: DCK Package
5-Pin SC70
Top View**



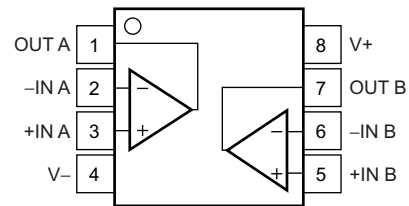
Pin Functions: TLV369

PIN		I/O	DESCRIPTION
NAME	TLV369 DCK (SC70)		
-IN	3	I	Negative (inverting) input
+IN	1	I	Positive (noninverting) input
OUT	4	O	Output
V-	2	—	Negative (lowest) power supply or ground (for single-supply operation)
V+	5	—	Positive (highest) power supply

**TLV2369: D Package
8-Pin SOIC
Top View**



**TLV2369: DGK Package
8-Pin VSSOP
Top View**



Pin Functions: TLV2369

PIN			I/O	DESCRIPTION
NAME	TLV2369			
	D (SOIC)	DGK (VSSOP)		
–IN A	2	2	I	Inverting input, channel A
–IN B	6	6	I	Inverting input, channel B
+IN A	3	3	I	Noninverting input, channel A
+IN B	5	5	I	Noninverting input, channel B
OUT A	1	1	O	Output, channel A
OUT B	7	7	O	Output, channel B
V–	4	4	—	Negative (lowest) power supply
V+	8	8	—	Positive (highest) power supply

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
Voltage	Supply, $V_S = (V+) - (V-)$	0	+7	V
	Signal input pin ⁽²⁾	$(V-) - 0.5$	$(V+) + 0.5$	V
Current	Signal input pin ⁽²⁾	–10	10	mA
	Output short-circuit ⁽³⁾	Continuous		mA
Temperature	Operating, T_A	–40	125	°C
	Junction, T_J		150	°C
	Storage, T_{stg}	–65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) Input pins are diode-clamped to the power-supply rails. Input signals that can swing more than 0.5 V beyond the supply rails must be current limited to 10 mA or less.
- (3) Short-circuit to $V_S / 2$, one amplifier per package.

6.2 ESD Ratings

over operating free-air temperature range (unless otherwise noted).

		VALUE	UNIT
$V_{(ESD)}$ Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±4000	V
	Charged device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1500	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted).

		MIN	NOM	MAX	UNIT
V_S	Supply voltage	1.8		5.5	V
	Specified temperature	–40		85	°C

6.4 Thermal Information: TLV369

THERMAL METRIC ⁽¹⁾		TLV369	UNIT
		DCK (SC70)	
		5 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	293.3	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	95.2	°C/W
R _{θJB}	Junction-to-board thermal resistance	83.4	°C/W
Ψ _{JT}	Junction-to-top characterization parameter	2.9	°C/W
Ψ _{JB}	Junction-to-board characterization parameter	82.4	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	n/a	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#).

6.5 Thermal Information: TLV2369

THERMAL METRIC ⁽¹⁾		TLV2369		UNIT
		D (SOIC)	DGK (VSSOP)	
		8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	121.5	168.5	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	66.3	58.1	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	62.5	88.9	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	22.8	9.3	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	61.9	87.6	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	n/a	n/a	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#).

6.6 Electrical Characteristics

V_S (total supply voltage) = 1.8 V to 5.5 V; at $T_A = 25^\circ\text{C}$, and $R_L = 100\text{ k}\Omega$ connected to $V_S / 2$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFFSET VOLTAGE						
V _{OS}	Input offset voltage	At T _A = 25°C		0.4	2	mV
		At T _A = −40°C to +85°C		0.85		
dV _{OS} /dT	Drift	At T _A = −40°C to +85°C		0.5		μV/°C
PSRR	Power-supply rejection ratio	V _S = 1.8 V to 5.5 V	80	94		dB
INPUT VOLTAGE RANGE						
V _{CM}	Common-mode voltage range		V−		V+	V
CMRR	Common-mode rejection ratio	(V−) ≤ V _{CM} ≤ (V+)	80	110		dB
INPUT BIAS CURRENT						
I _B	Input bias current	At T _A = 25°C		10		pA
		At T _A = −40°C to +85°C		See Figure 8		
I _{OS}	Input offset current			10		pA
INPUT IMPEDANCE						
Z _{ID}	Differential			10 ¹³ 3		Ω pF
Z _{IC}	Common-mode			10 ¹³ 6		Ω pF
NOISE						
E _n	Input voltage noise	f = 0.1 Hz to 10 Hz		4		μV _{PP}
e _n	Input voltage noise density	f = 1 kHz		300		nV/√Hz
i _n	Input current noise density	f = 1 kHz		1		fA/√Hz
OPEN-LOOP GAIN						
A _{OL}	Open-loop voltage gain	At V _S = 5.5 V, 100 mV ≤ V _O ≤ (V+) − 100 mV, R _L = 100 kΩ		130		dB
		At V _S = 5.5 V, 500 mV ≤ V _O ≤ (V+) − 500 mV, R _L = 10 kΩ	80	120		
OUTPUT						
V _O	Voltage output swing from rail	R _L = 10 kΩ			25	mV
I _{SC}	Short-circuit current			10		mA
C _{LOAD}	Capacitive load drive			See Figure 10		
FREQUENCY RESPONSE						
GBP	Gain bandwidth product			12		kHz
SR	Slew rate	G = 1		0.005		V/μs
t _{OR}	Overload recovery time	V _{IN} × gain = V _S		250		μs
POWER SUPPLY						
V _S	Specified voltage range		1.8		5.5	V
I _Q	Quiescent current	I _O = 0 mA, at V _S = 5.5 V		800	1300	nA
TEMPERATURE						
	Specified range		−40		85	°C
T _A	Operating range		−40		125	°C

6.7 Typical Characteristics

at $T_A = 25^\circ\text{C}$, $V_S = 5\text{ V}$, and $R_L = 100\text{ k}\Omega$ connected to $V_S / 2$ (unless otherwise noted)

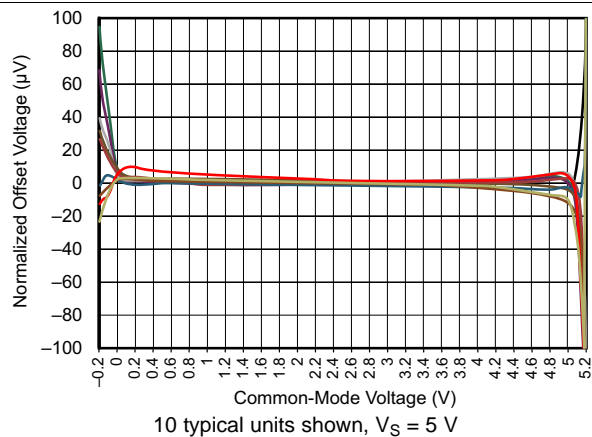


Figure 1. Normalized Offset Voltage vs Common-Mode Voltage

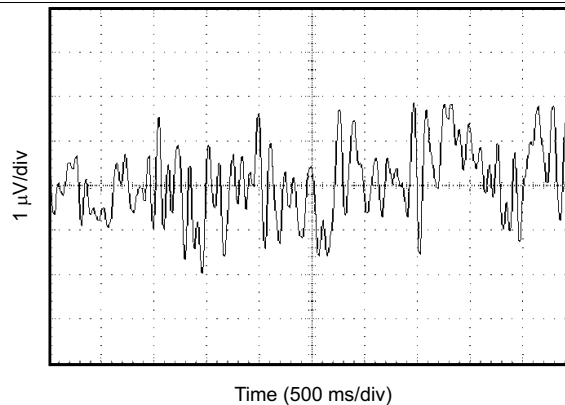


Figure 2. 0.1-Hz to 10-Hz Noise

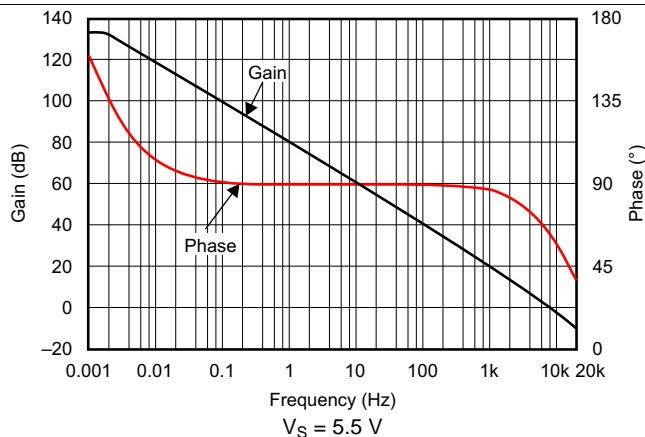


Figure 3. Open-Loop Gain and Phase vs Frequency

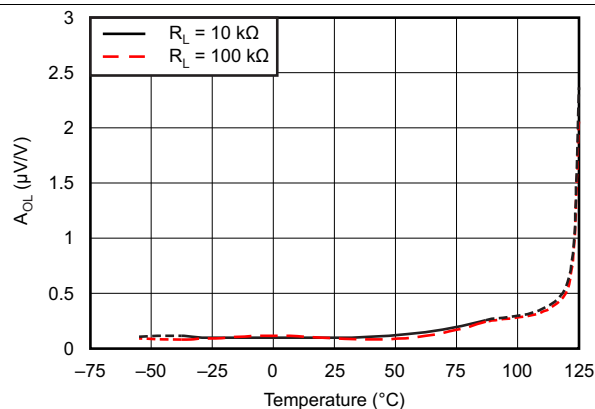


Figure 4. Open-Loop Gain vs Temperature

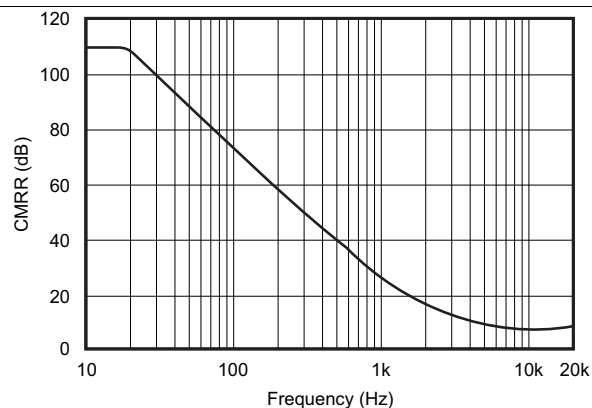


Figure 5. Common-Mode Rejection Ratio vs Frequency

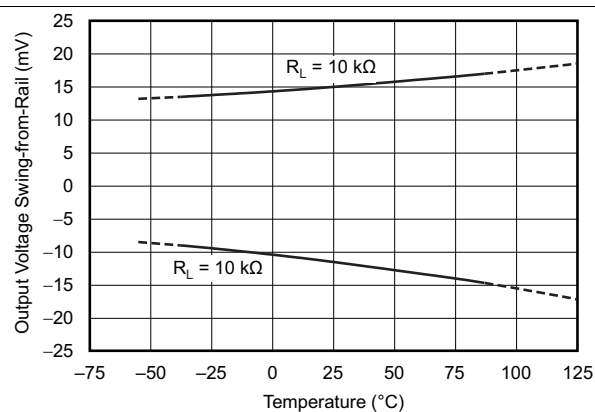


Figure 6. Output Voltage Swing from Rail vs Temperature

Typical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_S = 5\text{ V}$, and $R_L = 100\text{ k}\Omega$ connected to $V_S / 2$ (unless otherwise noted)

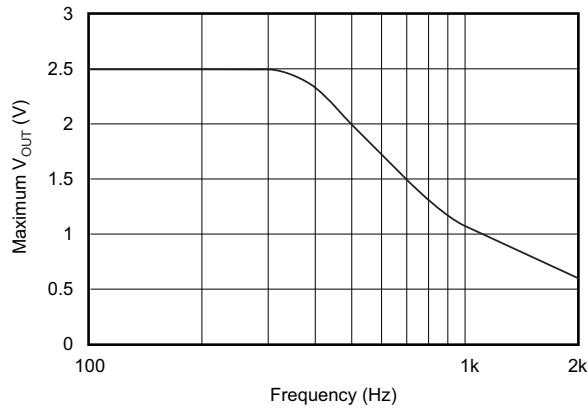


Figure 7. Maximum Output Voltage vs Frequency

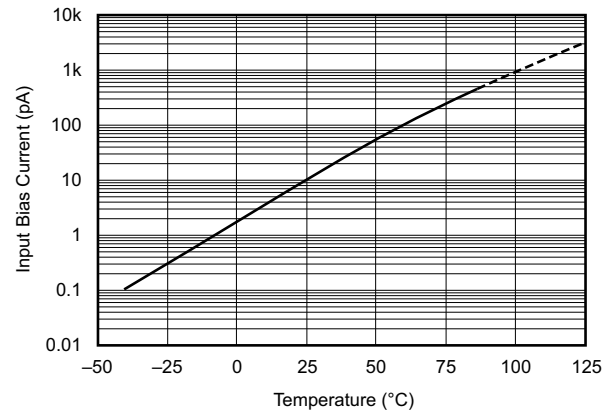


Figure 8. Input Bias Current vs Temperature

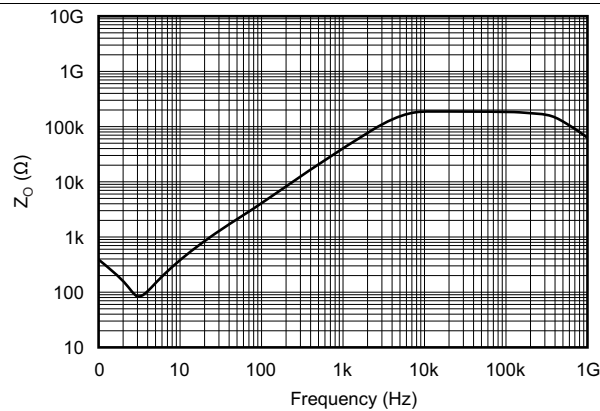


Figure 9. Open-Loop Output Impedance vs Frequency

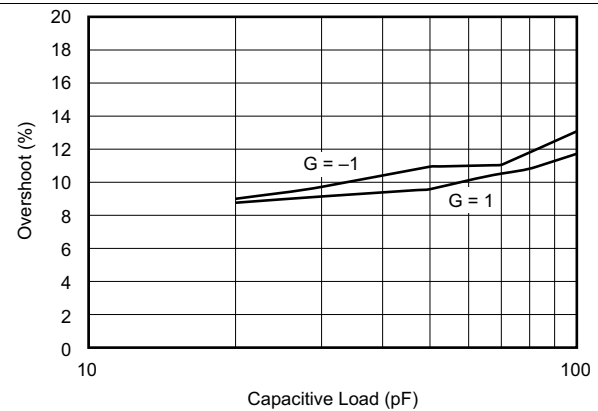


Figure 10. Small-Signal Overshoot vs Capacitive Load

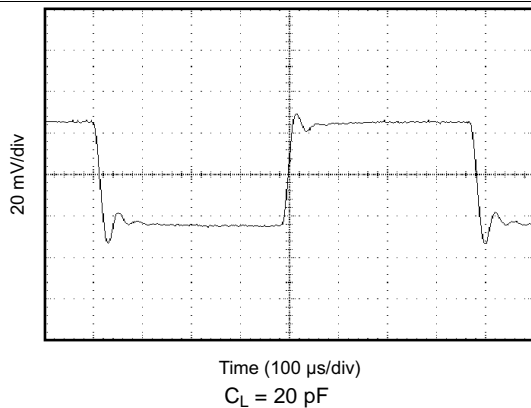


Figure 11. Small-Signal Step Response

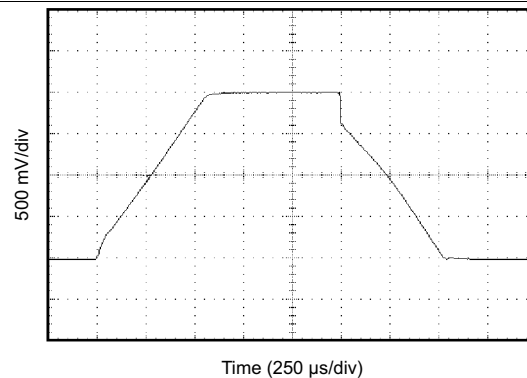


Figure 12. Large-Signal Step Response

Typical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_S = 5\text{ V}$, and $R_L = 100\text{ k}\Omega$ connected to $V_S / 2$ (unless otherwise noted)

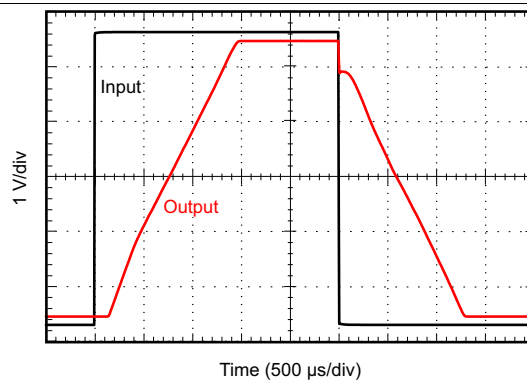


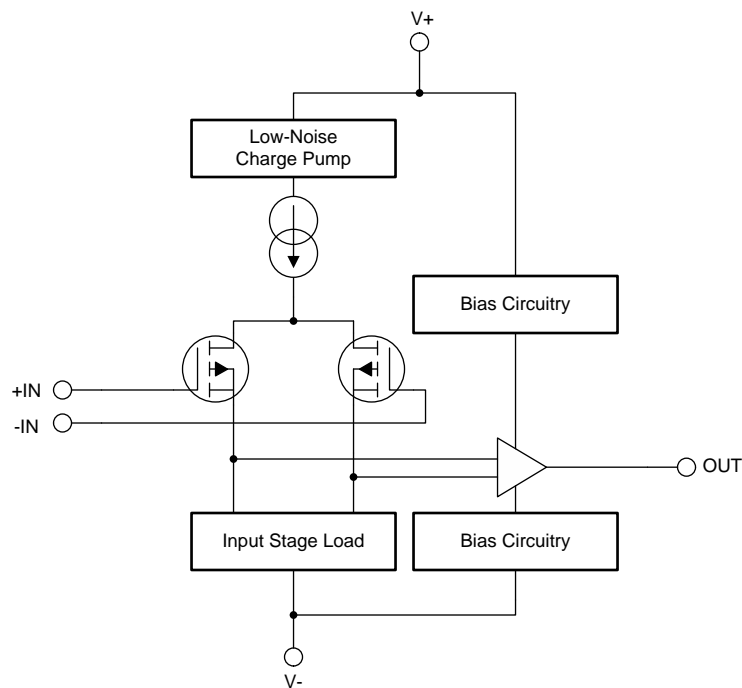
Figure 13. Overload Recovery

7 Detailed Description

7.1 Overview

The TLVx369 family of operational amplifiers minimizes power consumption and operates on supply voltages as low as 1.8 V. The zero-crossover distortion circuitry enables high linearity over the full input common-mode range, achieving true rail-to-rail input from a 1.8-V to 5.5-V single supply.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Operating Voltage

The TLV369 series op amps are fully specified and tested from 1.8 V to 5.5 V (± 0.9 V to ± 2.75 V). Parameters that vary significantly with supply voltage are described in the [Typical Characteristics](#) section.

7.3.2 Input Common-Mode Voltage Range

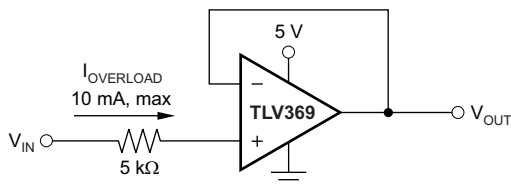
The TLV369 family is designed to eliminate the input offset transition region typically present in most rail-to-rail, complementary-stage operational amplifiers, allowing the TLV369 family of amplifiers to provide superior common-mode performance over the entire input range.

The input common-mode voltage range of the TLV369 family typically extends to each supply rail. CMRR is specified from the negative rail to the positive rail; see [Figure 1](#), *Normalized Offset Voltage vs Common-Mode Voltage*.

7.3.3 Protecting Inputs from Overvoltage

Input currents are typically 10 pA. However, large inputs (greater than 500 mV beyond the supply rails) can cause excessive current to flow in or out of the input pins. Therefore, in addition to keeping the input voltage between the supply rails, the input current must also be limited to less than 10 mA. This limiting is easily accomplished with an input resistor, as shown in [Figure 14](#).

A current-limiting resistor is required if the input voltage exceeds the supply rails by ≥ 0.5 V.



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Figure 14. Input Current Protection for Voltages That Exceed the Supply Voltage

7.4 Device Functional Modes

The TLV369 family has a single functional mode. These devices are powered on as long as the power-supply voltage is between 1.8 V (± 0.9 V) and 5.5 V (± 2.75 V).

8 Application and Implementation

NOTE

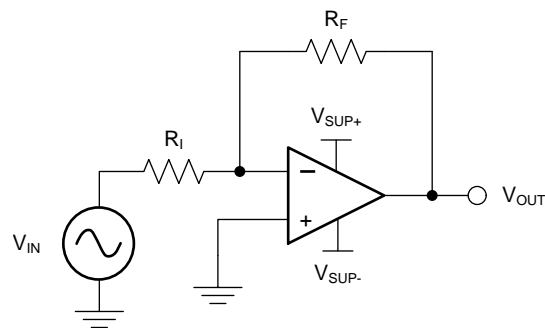
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

When designing for ultra-low power, choose system components carefully. To minimize current consumption, select large-value resistors. Any resistors can react with stray capacitance in the circuit and the input capacitance of the operational amplifier. These parasitic RC combinations can affect the stability of the overall system. Use of a feedback capacitor assures stability and limits overshoot or gain peaking.

8.2 Typical Application

A typical application for an operational amplifier is an inverting amplifier, as shown in [Figure 15](#). An inverting amplifier takes a positive voltage on the input and outputs a signal inverted to the input, making a negative voltage of the same magnitude. In the same manner, the amplifier also makes negative input voltages positive on the output. In addition, amplification can be added by selecting the input resistor R_I and the feedback resistor R_F .



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Figure 15. Application Schematic

8.2.1 Design Requirements

The supply voltage must be chosen to be larger than the input voltage range and the desired output range. The limits of the input common-mode range (V_{CM}) and the output voltage swing to the rails (V_O) must also be considered. For instance, this application scales a signal of ± 0.5 V (1 V) to ± 1.8 V (3.6 V). Setting the supply at ± 2.5 V is sufficient to accommodate this application.

Typical Application (continued)

8.2.2 Detailed Design Procedure

Determine the gain required by the inverting amplifier using [Equation 1](#) and [Equation 2](#):

$$A_V = \frac{V_{OUT}}{V_{IN}} \quad (1)$$

$$A_V = \frac{1.8}{-0.5} = -3.6 \quad (2)$$

When the desired gain is determined, choose a value for R_I or R_F . Choosing a value in the kilohm range is desirable for general-purpose applications because the amplifier circuit uses currents in the milliamp range. This milliamp current range ensures that the device does not draw too much current. The trade-off is that very large resistors (100s of kilohms) draw the smallest current but generate the highest noise. Very small resistors (100s of ohms) generate low noise but draw high current. This example uses 10 k Ω for R_I , meaning 36 k Ω is used for R_F . These values are determined by [Equation 3](#):

$$A_V = -\frac{R_F}{R_I} \quad (3)$$

8.2.3 Application Curve

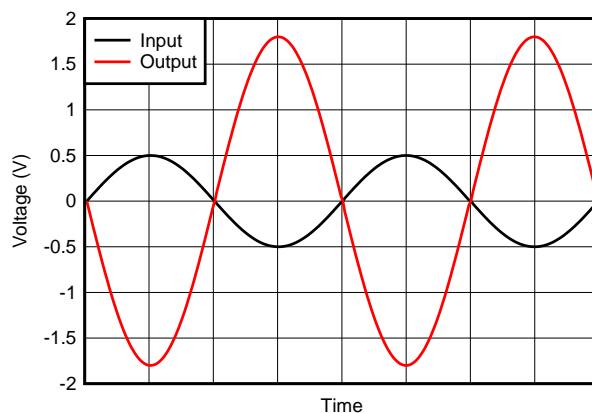
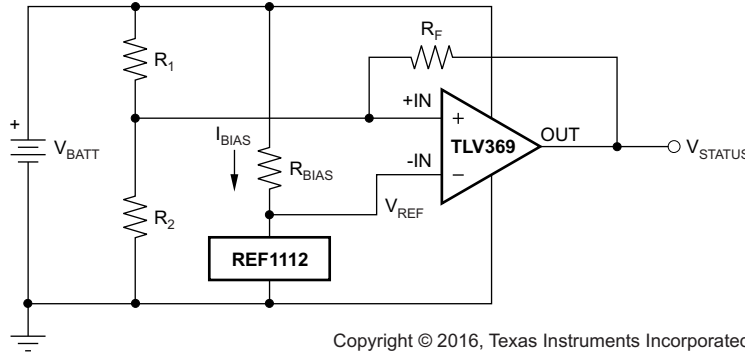


Figure 16. Inverting Amplifier Input and Output

8.3 System Examples

8.3.1 Battery Monitoring

The low operating voltage and quiescent current of the TLV369 series make the family an excellent choice for battery-monitoring applications, as shown in [Figure 17](#).



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Figure 17. Battery Monitor

In this circuit, V_{STATUS} is high as long as the battery voltage remains above 2 V. A low-power reference is used to set the trip point. Resistor values are selected as follows:

1. Selecting R_F : Select R_F such that the current through R_F is approximately 1000 times larger than the maximum bias current over temperature, as given by [Equation 4](#):

$$\begin{aligned} R_F &= \frac{V_{REF}}{1000 (I_{BMAX})} \\ &= \frac{1.2 \text{ V}}{1000 (50 \text{ pA})} \\ &= 24 \text{ M}\Omega \approx 20 \text{ M}\Omega \end{aligned} \quad (4)$$

2. Choose the hysteresis voltage, V_{HYST} . For battery-monitoring applications, 50 mV is adequate.
3. Calculate R_1 as calculated by [Equation 5](#):

$$R_1 = R_F \left(\frac{V_{HYST}}{V_{BATT}} \right) = 20 \text{ M}\Omega \left(\frac{50 \text{ mV}}{2.4 \text{ V}} \right) = 420 \text{ k}\Omega \quad (5)$$

4. Select a threshold voltage for V_{IN} rising (V_{THRS}) = 2.0 V.
5. Calculate R_2 as given by [Equation 6](#):

$$\begin{aligned} R_2 &= \frac{1}{\left[\left(\frac{V_{THRS}}{V_{BATT}} \right) - \frac{1}{R_1} - \frac{1}{R_1} \right]} \\ &= \frac{1}{\left[\left(\frac{2 \text{ V}}{1.2 \text{ V} \times 420 \text{ k}\Omega} \right) - \frac{1}{420 \text{ k}\Omega} - \frac{1}{20 \text{ M}\Omega} \right]} \\ &= 650 \text{ k}\Omega \end{aligned} \quad (6)$$

6. Calculate R_{BIAS} : The minimum supply voltage for this circuit is 1.8 V. The REF1112 has a current requirement of 1.2 μ A (max). Providing the REF1112 with 2 μ A of supply current assures proper operation. Therefore, R_{BIAS} is as given by [Equation 7](#).

$$R_{BIAS} = \frac{V_{BATTMIN}}{I_{BIAS}} = \frac{1.8 \text{ V}}{2 \text{ }\mu\text{A}} = 0.9 \text{ M}\Omega \quad (7)$$

System Examples (continued)

8.3.2 Window Comparator

Figure 18 shows the TLV2369 used as a window comparator. The threshold limits are set by V_H and V_L , with V_H greater than V_L . When V_{IN} is less than V_H , the output of A1 is low. When V_{IN} is greater than V_L , the output of A2 is low. Therefore, both op amp outputs are at 0 V as long as V_{IN} is between V_H and V_L . This architecture results in no current flowing through either diode, Q1 is in cutoff, with the base voltage at 0 V, and V_{OUT} forced high.

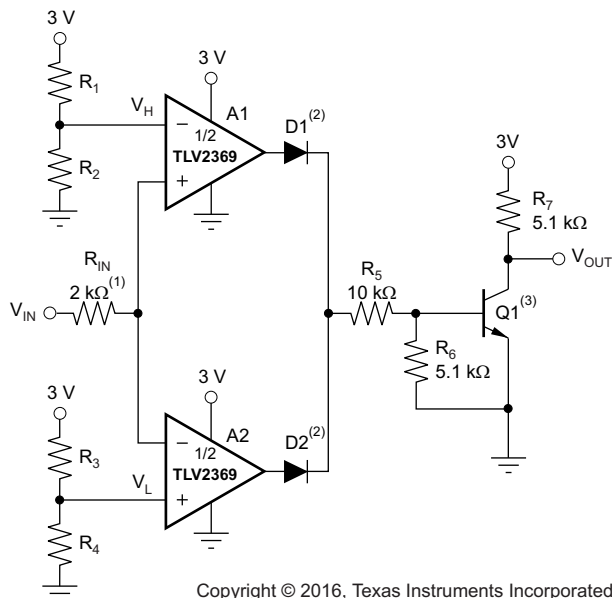


Figure 18. TLV2369 as a Window Comparator

If V_{IN} falls below V_L , the output of A2 is high, current flows through D2, and V_{OUT} is low. Likewise, if V_{IN} rises above V_H , the output of A1 is high, current flows through D1, and V_{OUT} is low. The window comparator threshold voltages are set as shown by Equation 8 and Equation 9:

$$V_H = \frac{R_2}{R_1 + R_2} \quad (8)$$

$$V_L = \frac{R_4}{R_3 + R_4} \quad (9)$$

9 Power Supply Recommendations

The TLV369 family is specified for operation from 1.8 V to 5.5 V (± 0.9 V to ± 2.75 V); many specifications apply from -40°C to $+125^\circ\text{C}$. The [Typical Characteristics](#) section presents parameters that can exhibit significant variance with regard to operating voltage or temperature.

CAUTION

Supply voltages larger than 7 V can permanently damage the device (see the [Absolute Maximum Ratings](#) table).

Place 0.1- μF bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or high-impedance power supplies. For more detailed information on bypass capacitor placement; see the [Layout Guidelines](#) section.

10 Layout

10.1 Layout Guidelines

For best operational performance of the device, use good printed circuit board (PCB) layout practices, including:

- Noise can propagate into analog circuitry through the power pins of the circuit as a whole and the operational amplifier. Use bypass capacitors to reduce the coupled noise by providing low-impedance power sources local to the analog circuitry.
 - Connect low-ESR, 0.1- μ F ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from $V+$ to ground is applicable for single-supply applications.
- Separate grounding for analog and digital portions of the circuitry is one of the simplest and most effective methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes. A ground plane helps distribute heat and reduces electromagnetic interference (EMI) noise pickup. Make sure to physically separate digital and analog grounds, paying attention to the flow of the ground current. For more detailed information, see *Circuit Board Layout Techniques*, [SLOA089](#).
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If these traces cannot be kept separate, crossing the sensitive trace perpendicularly is much better than crossing in parallel with the noisy trace.
- Place the external components as close to the device as possible. Keep R_F and R_G close to the inverting input in order to minimize parasitic capacitance, as shown in [Figure 19](#).
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.

10.2 Layout Example

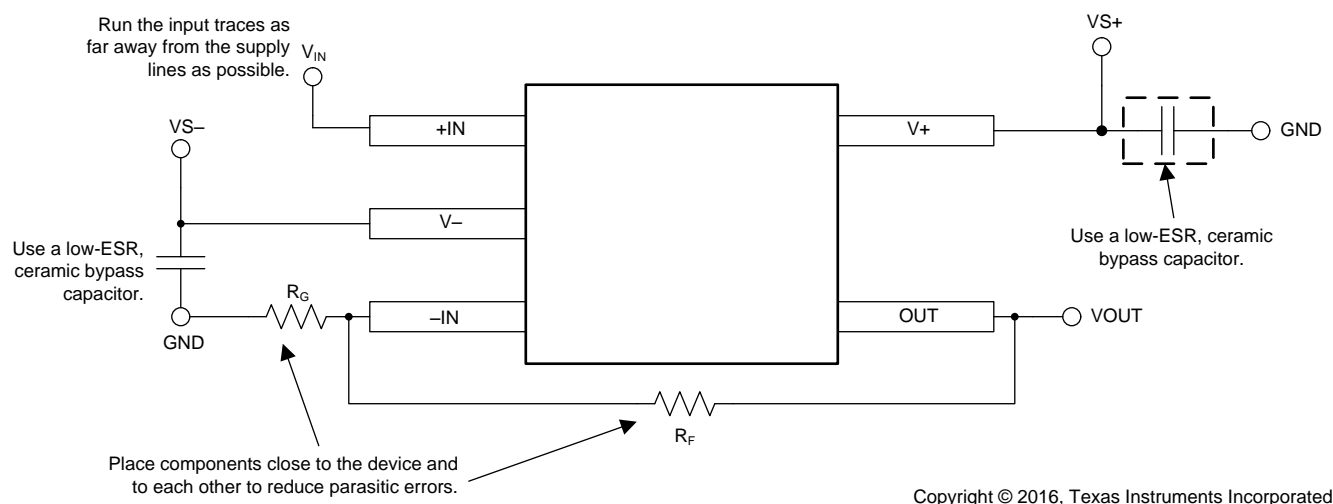
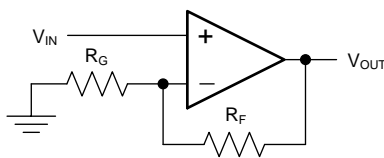


Figure 19. Operational Amplifier Board Layout for Noninverting Configuration



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Figure 20. Schematic Representation of [Figure 19](#)

11 器件和文档支持

11.1 文档支持

11.1.1 相关文档

使用 TLVx369 时，建议参考下列相关文档，文档下载地址为 www.ti.com.cn（除非另外注明）。

- 《REF1112 数据表》，[SBOS283](#)
- 《电路板布局布线技巧》，[SLOA089](#)
- 《运算放大器应用 手册》，[SBOA092](#)
- 《模拟工程师速查参考》，[SLWY038](#)

11.1.1.1 相关链接

表 1 列出了快速访问链接。范围包括技术文档、支持与社区资源、工具和软件，以及样片或购买的快速访问。

表 1. 相关链接

器件	产品文件夹	样片与购买	技术文档	工具与软件	支持与社区
TLV369	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处
TLV2369	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处

11.2 社区资源

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

11.3 商标

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

11.4 静电放电警告



ESD 可能会损坏该集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理措施和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

11.5 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

12 机械、封装和可订购信息

以下页中包括机械、封装和可订购信息。这些信息是针对指定器件可提供的最新数据。这些数据会在无通知且不对本文档进行修订的情况下发生改变。欲获得该数据表的浏览器版本，请查阅左侧的导航栏。

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TLV2369IDGKR	Active	Production	VSSOP (DGK) 8	2500 LARGE T&R	Yes	NIPDAU NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	13JV
TLV2369IDGKR.A	Active	Production	VSSOP (DGK) 8	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	13JV
TLV2369IDGKT	Active	Production	VSSOP (DGK) 8	250 SMALL T&R	Yes	NIPDAU NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	13JV
TLV2369IDGKT.A	Active	Production	VSSOP (DGK) 8	250 SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	13JV
TLV2369IDR	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TL2369
TLV2369IDR.A	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TL2369
TLV2369IDRG4	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TL2369
TLV2369IDRG4.A	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TL2369
TLV369IDCKR	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAU SN	Level-2-260C-1 YEAR	-40 to 125	12K
TLV369IDCKR.A	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	12K
TLV369IDCKR.B	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	12K
TLV369IDCKT	Active	Production	SC70 (DCK) 5	250 SMALL T&R	Yes	NIPDAU SN	Level-2-260C-1 YEAR	-40 to 125	12K
TLV369IDCKT.A	Active	Production	SC70 (DCK) 5	250 SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	12K
TLV369IDCKT.B	Active	Production	SC70 (DCK) 5	250 SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	12K

(1) **Status:** For more details on status, see our [product life cycle](#).

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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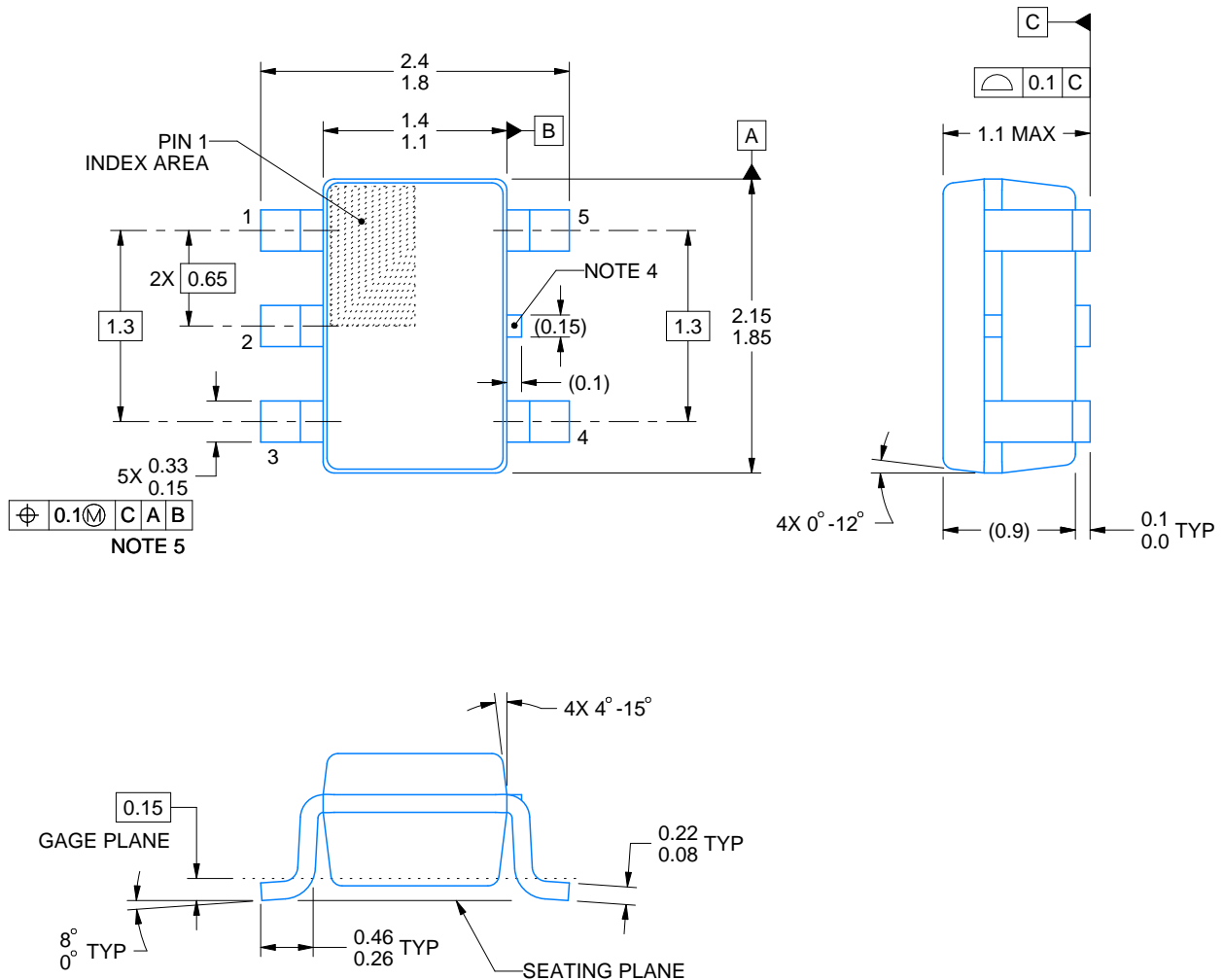
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DCK0005A

PACKAGE OUTLINE

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



4214834/G 11/2024

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC MO-203.
4. Support pin may differ or may not be present.
5. Lead width does not comply with JEDEC.
6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side

EXAMPLE BOARD LAYOUT

DCK0005A

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:18X



SOLDER MASK DETAILS

4214834/G 11/2024

NOTES: (continued)

7. Publication IPC-7351 may have alternate designs.
8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 THICK STENCIL
SCALE:18X

4214834/G 11/2024

NOTES: (continued)

9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
10. Board assembly site may have different recommendations for stencil design.

D0008A**PACKAGE OUTLINE****SOIC - 1.75 mm max height**

SMALL OUTLINE INTEGRATED CIRCUIT



4214825/C 02/2019

NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.125 MM] THICK STENCIL
SCALE:8X

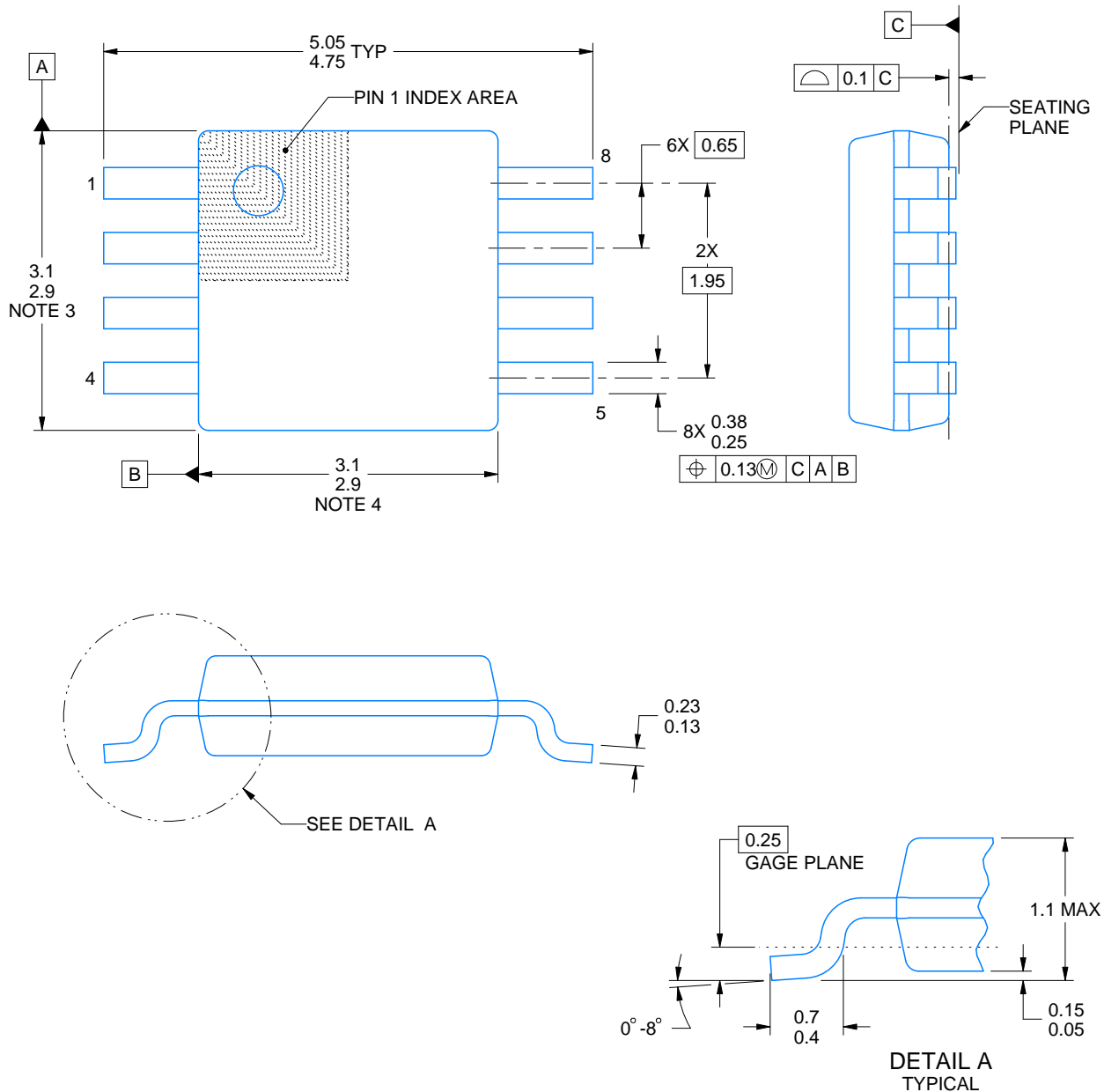
4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

DGK0008A**PACKAGE OUTLINE****VSSOP - 1.1 mm max height**

SMALL OUTLINE PACKAGE



4214862/A 04/2023

NOTES:

PowerPAD is a trademark of Texas Instruments.

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-187.

EXAMPLE BOARD LAYOUT

DGK0008A

™ VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 15X



SOLDER MASK DETAILS

4214862/A 04/2023

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
8. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.
9. Size of metal pad may vary due to creepage requirement.

EXAMPLE STENCIL DESIGN

DGK0008A

TM VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
SCALE: 15X

4214862/A 04/2023

NOTES: (continued)

11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
12. Board assembly site may have different recommendations for stencil design.

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